

Silicon NPN Power Transistors

2SD717

DESCRIPTION

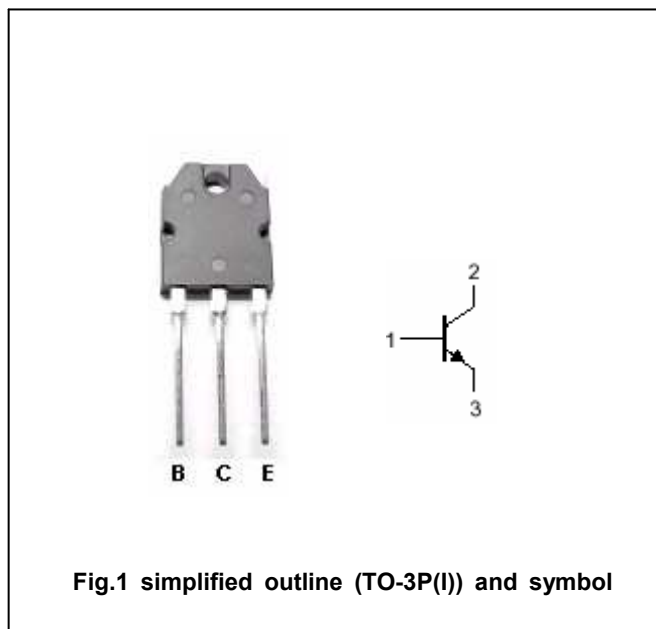
- With TO-3P(I) package
- Low collector saturation voltage
- High collector power dissipation

APPLICATIONS

- High power switching applications
- DC-DC converter and DC-AC inverter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	70	V
V_{CEO}	Collector-emitter voltage	Open base	50	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
I_B	Base current		2	A
P_T	Total power dissipation	$T_C=25^\circ$	80	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA, I_B=0$	50			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A; I_B=0.3A$			0.4	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A; I_B=0.3A$			1.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=70V; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=1A; V_{CE}=1V$	70		240	
h_{FE-2}	DC current gain	$I_C=6A; V_{CE}=1V$	30			
f_T	Transition frequency	$I_C=1A; V_{CE}=4V$		10		MHz
C_{ob}	Output capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		350		pF

Switching times

t_{on}	Turn-on time	$I_{B1}=-I_{B2}=0.3A; R_L=5\Omega; V_{CC}=30V$		0.3		μs
t_s	Storage time			2.5		μs
t_f	Fall time			0.4		μs

◆ h_{FE-1} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

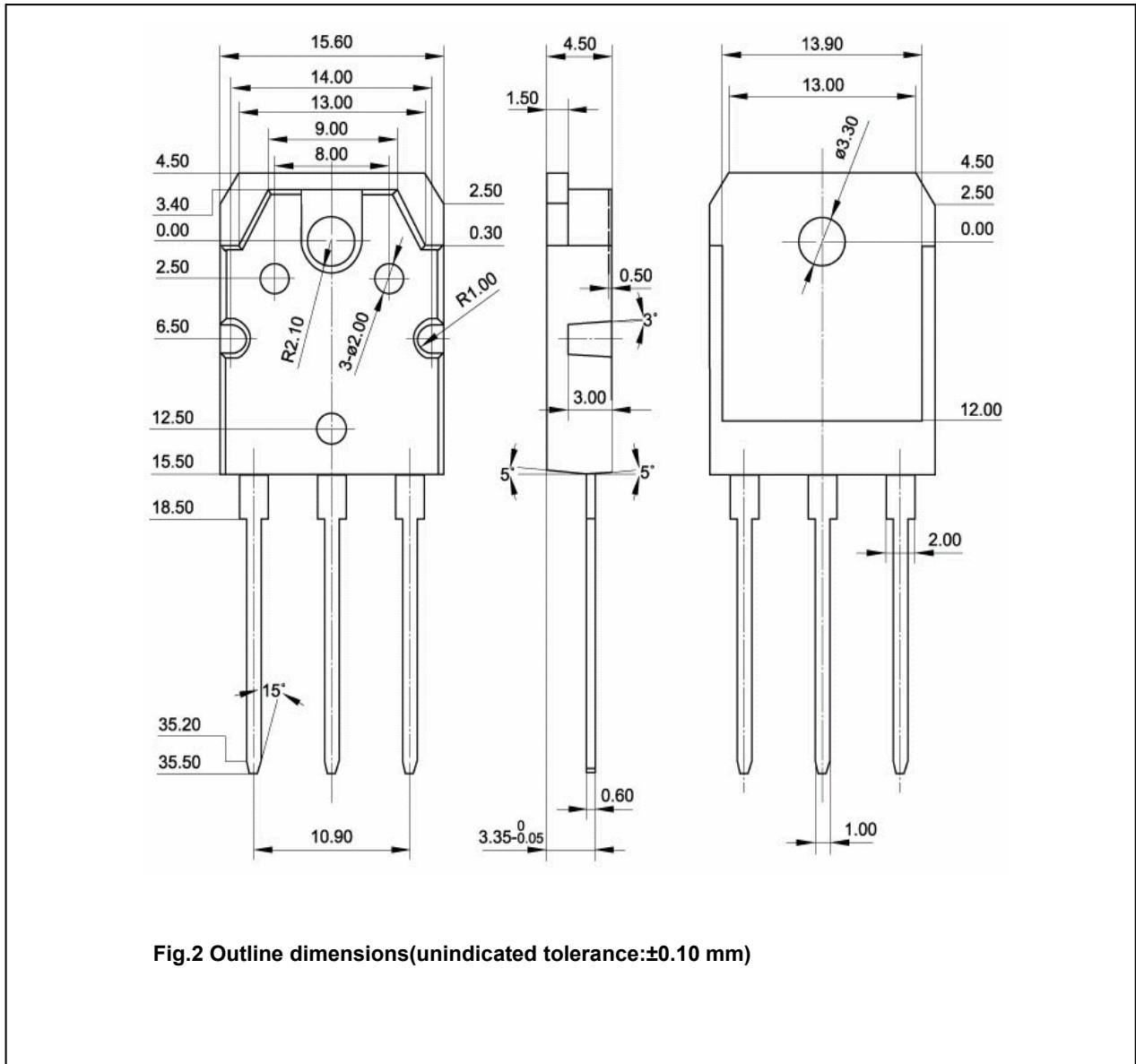


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.